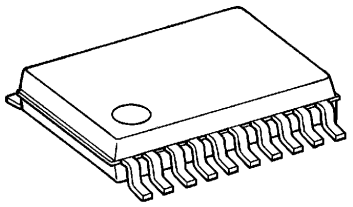
TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7MZ244FK

LOW VOLTAGE OCTAL BUS BUFFER WITH 5V TOLERANT INPUTS AND OUTPUTS

The TC7MZ244 is a high performance CMOS OCTAL BUS BUFFER. Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.
The device is designed for low-voltage (3.3 V) V_{CC} applications, but it could be used to interface to 5 V supply environment for both inputs and outputs.
The TC7MZ244 is a non-inverting 3-state buffer having two active-low output enables. This device is designed to be used with 3-state memory address drivers, etc.
All inputs are equipped with protection circuits against static discharge.



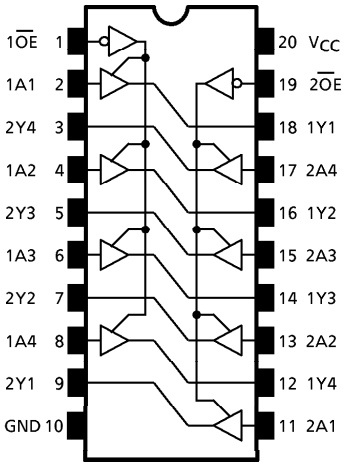
VSSOP20-P-0030-0.50

Weight : 0.03 g (typ.)

Features

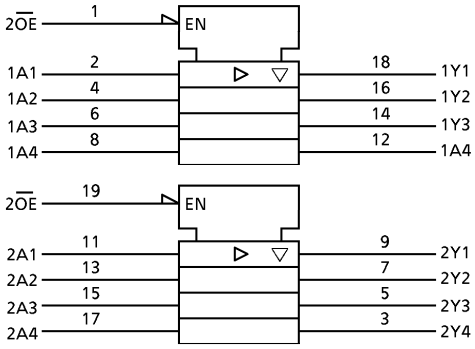
- Low voltage operation : V_{CC} = 2.0~3.6 V
- High speed operation : t_{pd} = 6.5 ns (max) (V_{CC} = 3.0~3.6 V)
- Output current : $|I_{OH}| / I_{OL}$ = 24 mA (min) (V_{CC} = 3.0 V)
- Latch-up performance : ± 500 mA
- Available in VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Pin and function compatible with the 74 series (74AC / VHC / HC / F / ALS / LS etc.) 244 type.

Pin Assignment



(TOP VIEW)

IEC Logic Symbol



Truth Table

INPUTS		OUTPUTS
$\overline{OE}$	An	
L	L	L
L	H	H
H	X	Z

X : Don't Care
Z : High Impedance

Maximum Ratings

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	−0.5~7.0	V
DC Input Voltage	V_{IN}	−0.5~7.0	V
DC Output Voltage	V_{OUT}	−0.5~7.0 (Note 1)	V
		−0.5~V_{CC} + 0.5 (Note 2)	
Input Diode Current	I_{IK}	−50	mA
Output Diode Current	I_{OK}	±50 (Note 3)	mA
DC Output Current	I_{OUT}	±50	mA
Power Dissipation	P_D	180	mW
DC V_{CC}/Ground Current	I_{CC} / I_{GND}	±100	mA
Storage Temperature	T_{stg}	−65~150	°C

(Note 1): Output in Off-State
(Note 2): High or Low State. I_{OUT} absolute maximum rating must be observed.
(Note 3): $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Conditions

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2.0~3.6	V
		1.5~3.6 (Note 4)	
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~5.5 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH} / I_{OL}	±24 (Note 7)	mA
		±12 (Note 8)	
Operating Temperature	T_{opr}	−40~85	°C
Input Rise And Fall Time	dt / dv	0~10 (Note 9)	ns / V

(Note 4): Data Retention Only
(Note 5): Output in Off-State
(Note 6): High or Low State
(Note 7): V_{CC} = 3.0~3.6 V
(Note 8): V_{CC} = 2.7~3.0 V
(Note 9): V_{IN} = 0.8~2.0 V, V_{CC} = 3.0 V

Electrical Characteristics

DC characteristics (Ta = −40~85°C)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	Min	Max	UNIT
Input Voltage	"H" Level	V_{IH}			2.7~3.6	2.0	—	V
	"L" Level	V_{IL}			2.7~3.6	—	0.8	
Output Voltage	"H" Level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −100 μA	2.7~3.6	V_{CC} − 0.2	—	V
				I_{OH} = −12 mA	2.7	2.2	—	
				I_{OH} = −18 mA	3.0	2.4	—	
				I_{OH} = −24 mA	3.0	2.2	—	
	"L" Level	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 100 μA	2.7~3.6	—	0.2	
				I_{OL} = 12 mA	2.7	—	0.4	
				I_{OL} = 16 mA	3.0	—	0.4	
				I_{OL} = 24 mA	3.0	—	0.55	
Input Leakage Current		I_{IN}	V_{IN} = 0~5.5 V		2.7~3.6	—	±5.0	μA
3-State Output Off-State Current		I_{OZ}	V_{IN} = V_{IH} or V_{IL} V_{OUT} = 0~5.5 V		2.7~3.6	—	±5.0	μA
Power Off Leakage Cuurent		I_{OFF}	V_{IN} / V_{OUT} = 5.5 V		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		2.7~3.6	—	10.0	μA
			V_{IN} / V_{OUT} = 3.6~5.5 V		2.7~3.6	—	±10.0	
Increase In I_{CC} Per Input		ΔI_{CC}	V_{IH} = V_{CC} − 0.6 V		2.7~3.6	—	500	μA

AC Characteristic (Ta = −40~85°C)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Min	Max	UNIT
Propagation Delay Time	t_{pLH} t_{pHL}	(Fig.1, 2)	2.7	—	7.5	ns
			3.3 ± 0.3	1.5	6.5	
Output Enable Time	t_{pZL} t_{pZH}	(Fig.1, 3)	2.7	—	9.0	ns
			3.3 ± 0.3	1.5	8.0	
Output Disable Time	t_{pLZ} t_{pHZ}	(Fig.1, 3)	2.7	—	8.0	ns
			3.3 ± 0.3	1.5	7.0	
Output To Output Skew	t_{osLH} t_{osHL}	(Note 10)	2.7	—	—	ns
			3.3 ± 0.3	—	1.0	

(Note 10): Parameter guaranteed by design.
($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

Dynamic Switching Characteristics (Ta = 25°C, Input $t_r = t_f = 2.5$ ns, $C_L = 50$ pF, $R_L = 500\ \Omega$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Typ.	UNIT
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	V_{IH} = 3.3 V, V_{IL} = 0 V	3.3	0.8	V
Quiet Output Minimum Dynamic V_{OL}	$\|V_{OLV}\|$	V_{IH} = 3.3 V, V_{IL} = 0 V	3.3	0.8	V

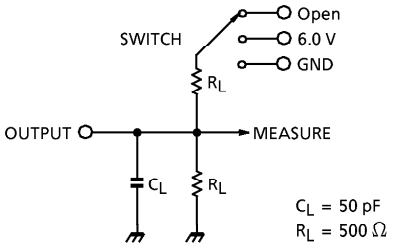
Capacitive Characteristics (Ta = 25°C)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Typ.	UNIT
Input Capacitance	C_{IN}	—	3.3	7	pF
Output Capacitance	C_{OUT}		3.3	8	pF
Power Dissipation Capacitance	C_{PD}	f_{IN} = 10 MHz (Note 11)	3.3	25	pF

(Note 11): C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.
Average operating current can be obtained by the equation :
$I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 8$ (per bit)

Test Circuit

Fig.1



PARAMETER	SWITCH
t_{pLH}, t_{pHL}	Open
t_{pLZ}, t_{pZL}	6.0 V
t_{pHZ}, t_{pZH}	GND

AC Waveform

Fig.2 t_{pLH}, t_{pHL}

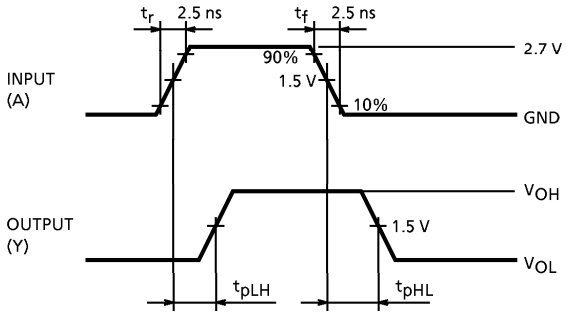
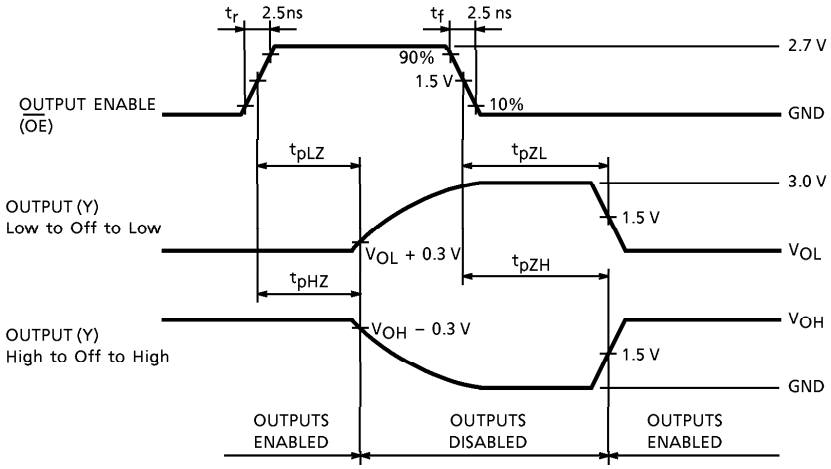
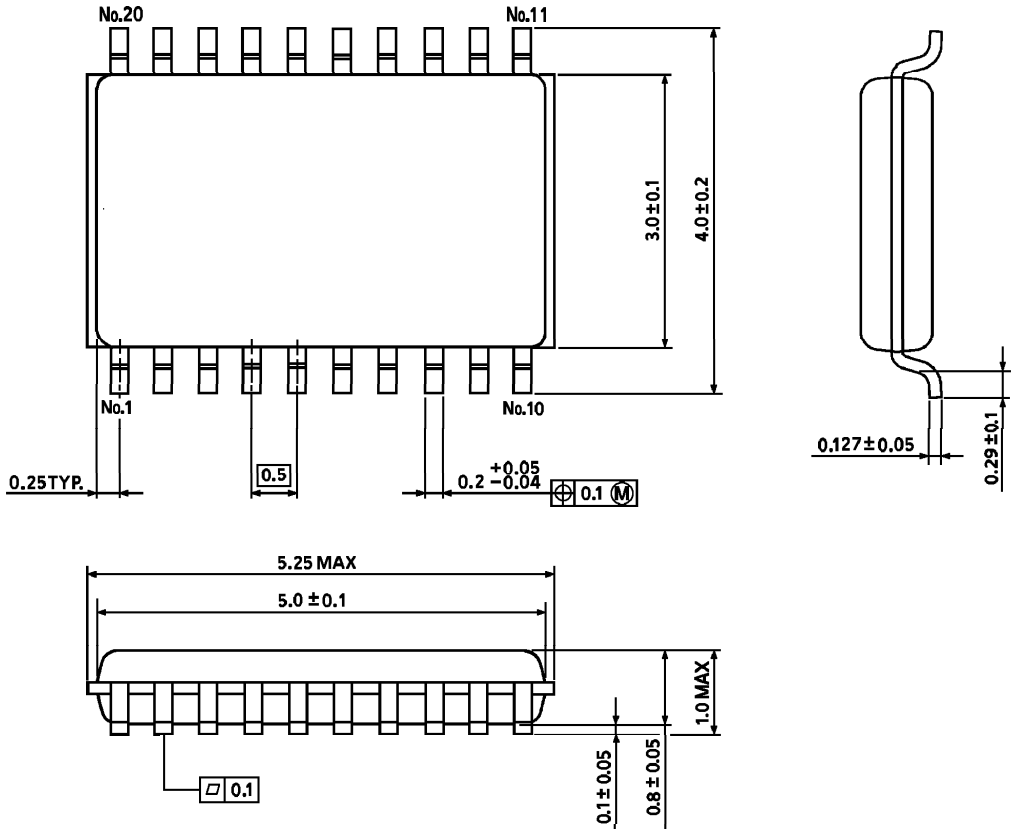


Fig.3 t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}



Outline Drawing

VSSOP20-P-0030-0.50 Unit : mm



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